

Acrit
encapsulating resin 5 for sealing the parts inclusive of the semiconductor chip 1 and the metal thin wires 4.--

Page 3, please replace the second paragraph bridging lines 10-15 with the following replacement paragraph:

A2
--Defoaming is performed as needed upon charging of the encapsulating resin 5 to break or vanish foam which remain in the encapsulating resin 5, and a uniform sealed portion is formed after its curing, whereby a semiconductor device free of a reduction in reliability due to trapped moisture or the like is completed.--

Page 8, line 10, through Page 9, line 6, please replace the paragraphs with the following replacement paragraphs:

3
--For example, a B-staged epoxy resin used as the B-staged thermosetting resin needs care such as the need for cold storing processing to manage its reaction probability. However, the B-staged epoxy resin can be expected to have high adhesion. Further, the thermoplastic resin is easy to handle, and the mixed material has characteristics of the two referred to above.

While the semiconductor chip 1 is fixedly secured to the heat spreader 3 by the adhesive layer 12 rather than with the conventional die attach material, a high thermal-conductive adhesive is also known and can be also set to the same thermal conductivity as the die attach material. Even in the case of the die attach material and the adhesive, no serious influence occurs in terms of a heat dissipation property of a package.

3
A 3
According to the first embodiment as described above, since the semiconductor chip 1 and the wiring board 2 are fixed to the heat spreader 3 by the adhesive layer 12 provided over the entire principal surface of the heat spreader 3, the conventional recessed portion of adhesive does not occur between the wiring board 2 and the heat spreader 3, so that voids can be prevented from occurring in an encapsulating process step.--

Page 11, line 27, through Page 12, line 10, please replace the paragraphs with the following replacement paragraphs:

14
A 4
--According to the second embodiment as described above, since the adhesive layers 12 and 14 are identical in thermal characteristic and are formed over the principal surface and reverse side of the heat spreader 3, in addition to the effect obtained in the first embodiment, warpage can be reduced even if the heat spreader 3 and the adhesive layers 12 and 14 are different in thermal expansion characteristic from one another. It is thus possible to realize a semiconductor device wherein a wiring board 2 and the heat spreader 3 have good adhesive properties and a reduction in warpage is reached.--

Page 14, line 23, through Page 15, line 5, please replace the paragraphs with the following replacement paragraphs:

5
A 5
--In a process step (a), a frame-shaped first adhesive layer 16 is formed over the principal surface of the heat spreader 3. The wiring board 2 is fixed to the heat spreader 3 with the first adhesive layer 16 interposed therebetween.